Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(((polysilicon or polySi or silicon) adj gate) and (dielectric adj cap) and (silicide$2 with source$drain) and substrate and (dielectric with stack) and (lower adj dielectric adj layer) and (upperr adj dielectric adj layer) and (polish$3 or planariz$3) and (etch$3 with selective$3) and salicid$3 and work$function and implant$5).CLM.	US-PGPUB	OR	ON	2006/01/29 13:16